



# 150mA CMOS LDO Regulator

## FEATURES

- Guaranteed 150mA output current
- Low dropout voltage of 90mV typical at 150mA
- Stable with 1 $\mu$ F ceramic output capacitor
- External 10nF bypass capacitor for low noise
- Quick-start feature
- No-load ground current of 55 $\mu$ A typical
- Full-load ground current of 80 $\mu$ A typical
- $\pm 1.0\%$  output voltage initial accuracy
- $\pm 2.0\%$  accuracy over temperature
- “Zero” current shutdown mode
- Current limit and Under voltage lockout
- Thermal protection
- Thin SOT23-5 package

## APPLICATIONS

- Cellular phones
- Battery-powered devices
- Consumer Electronics

For Ordering Information details, see page 9.

## DESCRIPTION

The CAT6217 is a 150mA CMOS low dropout regulator that provides fast response time during load current and line voltage changes.

The quick-start feature allows the use of an external bypass capacitor to reduce the overall output noise without affecting the turn-on time of just 150 $\mu$ s.

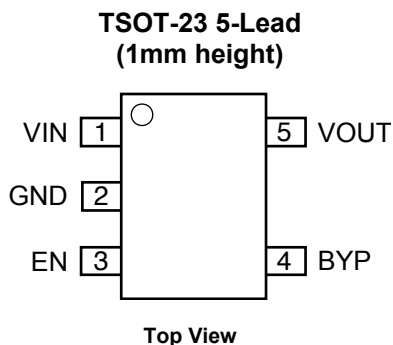
With zero shutdown current and low ground current of 55 $\mu$ A typical, the CAT6217 is ideal for battery-operated devices with supply voltages from 2.3V to 5.5V. An internal under voltage lockout circuit disables the output at supply voltages under 2.1V typical.

The CAT6217 offers 1% initial accuracy and low dropout voltage, 90mV typical at 150mA. Stable operation is provided with a 1 $\mu$ F ceramic capacitor, reducing required board space and component cost.

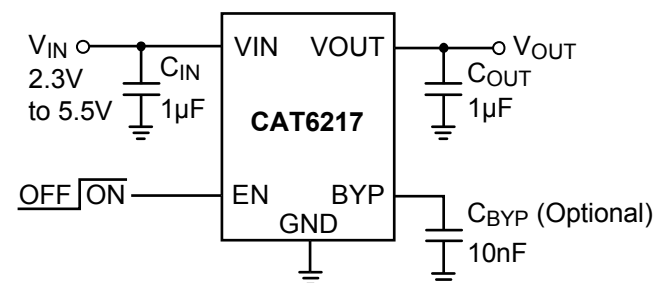
Other features include output short-circuit current limit and thermal protection.

The device is available in the low profile (1mm max height) 5-lead thin SOT23 package.

## PIN CONFIGURATION



## TYPICAL APPLICATION CIRCUIT



**PIN DESCRIPTIONS**

Pin #	Name	Function
1	VIN	Supply voltage input.
2	GND	Ground reference.
3	EN	Enable input (active high); a 2.5MΩ pull-down resistor is provided.
4	BYP	Optional bypass capacitor connection for noise reduction and PSRR enhancing.
5	VOUT	LDO Output Voltage.

**BLOCK DIAGRAM**

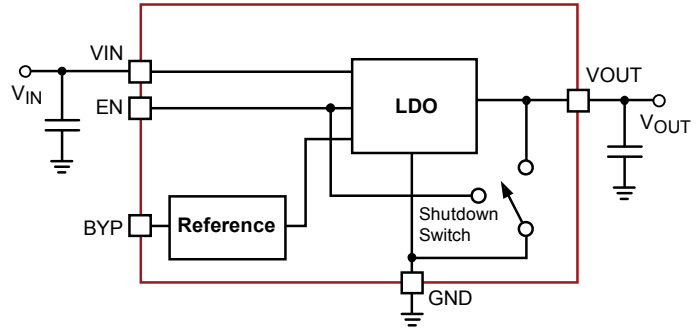


Figure 2. CAT6217 Functional Block Diagram

**PIN FUNCTION**

**VIN** is the supply pin for the LDO. A small 1μF ceramic bypass capacitor is required between the V<sub>IN</sub> pin and ground near the device. When using longer connections to the power supply, C<sub>IN</sub> value can be increased without limit. The operating input voltage range is from 2.3V to 5.5V.

**EN** is the enable control logic (active high) for the regulator output. It has a 2.5MΩ pull-down resistor, which assures that if EN pin is left open, the circuit is disabled.

**VOUT** is the LDO regulator output. A small 1μF ceramic bypass capacitor is required between the V<sub>OUT</sub> pin and ground for stability. For better transient response, its value can be increased to 4.7μF.

The capacitor should be located near the device. ESR domain is 5mΩ to 500mΩ. V<sub>OUT</sub> can deliver a maximum guaranteed current of 150mA. A 250Ω internal shutdown switch discharges the output capacitor in the no-load condition.

**GND** is the ground reference for the LDO. The pin must be connected to the ground plane on the PCB.

**BYP** is the reference bypass pin. An optional 0.01μF capacitor can be connected between BYP pin and GND to reduce the output noise and enhance the PSRR at high frequency.

**ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>**

Parameter	Rating	Unit
V <sub>IN</sub>	0 to 6.5	V
V <sub>EN</sub> , V <sub>OUT</sub>	-0.3 to V <sub>IN</sub> +0.3	V
Junction Temperature, T <sub>J</sub>	+150	°C
Power Dissipation, P <sub>D</sub>	Internally Limited <sup>(2)</sup>	mW
Storage Temperature Range, T <sub>S</sub>	-65 to +150	°C
Lead Temperature (soldering, 5 sec.)	260	°C
ESD Rating (Human Body Model)	3	kV

**RECOMMENDED OPERATING CONDITIONS <sup>(3)</sup>**

Parameter	Range	Unit
V <sub>IN</sub>	2.3 to 5.5	V
V <sub>EN</sub>	0 to V <sub>IN</sub>	V
Junction Temperature Range, T <sub>J</sub>	-40 to +125	°C
Package Thermal Resistance (SOT23-5), θ <sub>JA</sub>	235	°C/W

Typical application circuit with external components is shown on page 1.

**Notes:**

- (1) Exceeding maximum rating may damage the device
- (2) The maximum allowable power dissipation at any T<sub>A</sub> (ambient temperature) is P<sub>Dmax</sub> = (T<sub>Jmax</sub> - T<sub>A</sub>)/θ<sub>JA</sub>. Exceeding the maximum allowable power dissipation will result in excessive die temperature, and the regulator will go into thermal shutdown.
- (3) The device is not guaranteed to work outside its operating rating.

**ELECTRICAL OPERATING CHARACTERISTICS <sup>(1)</sup>**
 $V_{IN} = V_{OUT} + 1.0V$ ,  $V_{EN} = \text{High}$ ,  $I_{OUT} = 100\mu A$ ,  $C_{IN} = C_{OUT} = 1\mu F$ , ambient temperature of 25°C (over recommended operating conditions unless specified otherwise). **Bold numbers** apply for the entire junction temperature range.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{OUT-ACC}$	Output Voltage Accuracy	Initial accuracy	-1.0		+1.0	%
			<b>-2.0</b>		<b>+2.0</b>	
$TC_{OUT}$	Output Voltage Temp. Coefficient			40		ppm/°C
$V_{R-LINE}$	Line Regulation	$V_{IN} = V_{OUT} + 1.0V$ to 5.5V	-0.2	±0.1	+0.2	%V
			<b>-0.4</b>		<b>+0.4</b>	
$V_{R-LOAD}$	Load Regulation	$I_{OUT} = 100\mu A$ to 150 mA		0.6	1.0	%
					<b>1.3</b>	
$V_{DROP}$	Dropout Voltage <sup>(2)</sup>	$I_{OUT} = 150mA$		90	125	mV
					<b>150</b>	
$I_{GND}$	Ground Current	$I_{OUT} = 0\mu A$		55	75	$\mu A$
		$I_{OUT} = 150mA$		80		
$I_{GND-SD}$	Shutdown Ground Current	$V_{EN} < 0.4V$			1	$\mu A$
					<b>2</b>	
PSRR	Power Supply Rejection Ratio	$f = 1kHz$ , $C_{BYP} = 10nF$		64		dB
		$f = 20kHz$ , $C_{BYP} = 10nF$		54		
$I_{SC}$	Output short circuit current limit	$V_{OUT} = 0V$		350		mA
$T_{ON}$	Turn-On Time	$C_{BYP} = 10nF$		150		$\mu s$
$e_N$	Output Noise Voltage <sup>(3)</sup>	BW = 10Hz to 100kHz		45		$\mu V_{rms}$
$R_{OUT-SH}$	Shutdown Switch Resistance			250		$\Omega$
$R_{EN}$	Enable pull-down resistor			2.5		M $\Omega$
$V_{UVLO}$	Under-voltage lock out (UVLO) threshold			2.1		V
ESR	$C_{OUT}$ equivalent series resistance		5		500	m $\Omega$
<b>Enable Input</b>						
$V_{HI}$	Logic High Level	$V_{IN} = 2.3$ to 5.5V	<b>1.8</b>			V
$V_{LO}$	Logic Low Level	$V_{IN} = 2.3$ to 5.5V			<b>0.4</b>	V
$I_{EN}$	Enable Input Current	$V_{EN} = 0.4V$		0.15	<b>1</b>	$\mu A$
		$V_{EN} = V_{IN}$		1.5	<b>4</b>	
<b>Thermal Protection</b>						
$T_{SD}$	Thermal Shutdown			160		°C
$T_{HYS}$	Thermal Hysteresis			10		°C

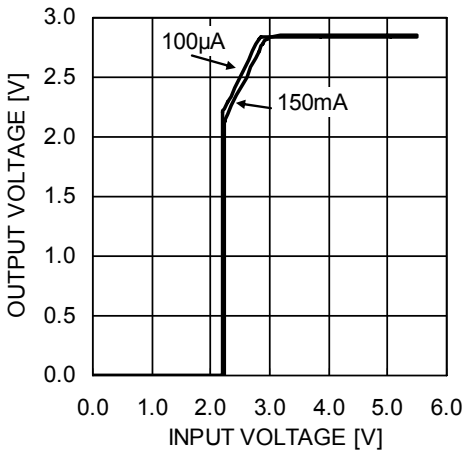
**Notes:**

- (1) Specification for 2.85V output version unless specified otherwise.
- (2) Dropout voltage is defined as the input-to-output differential at which the output voltage drops 2% below its nominal value measured at 1V differential. During test, the input voltage stays always above the minimum 2.3V.
- (3) Specification for 1.8V output version.

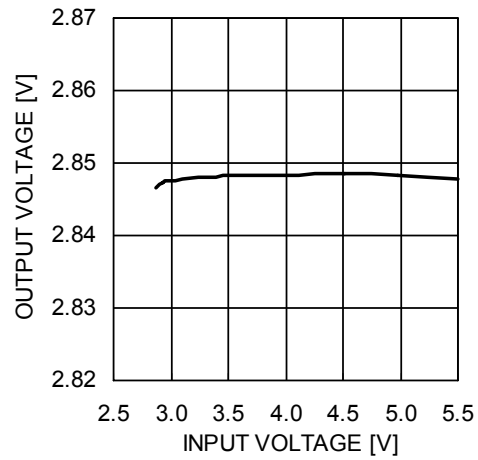
**TYPICAL CHARACTERISTICS** (shown for 2.85V output version)

$V_{IN} = 3.85V$ ,  $I_{OUT} = 100\mu A$ ,  $C_{IN} = C_{OUT} = 1\mu F$ ,  $C_{BYP} = 10nF$ ,  $T_A = 25^\circ C$  unless otherwise specified.

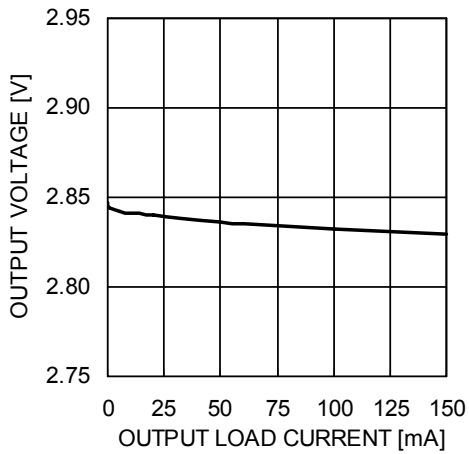
**Dropout Characteristics**



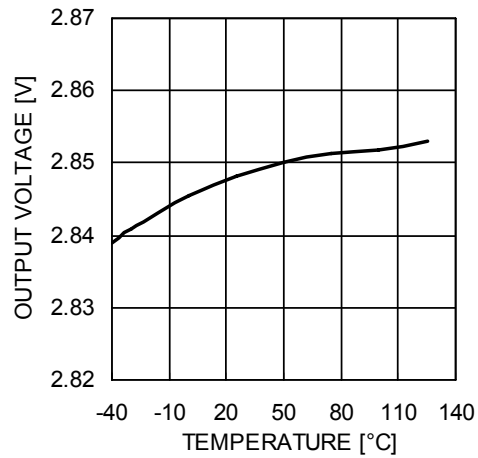
**Line Regulation**



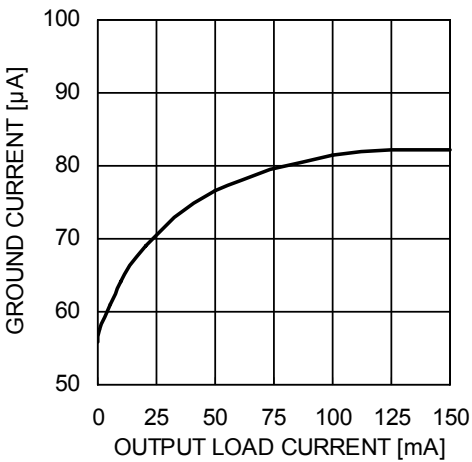
**Load Regulation**



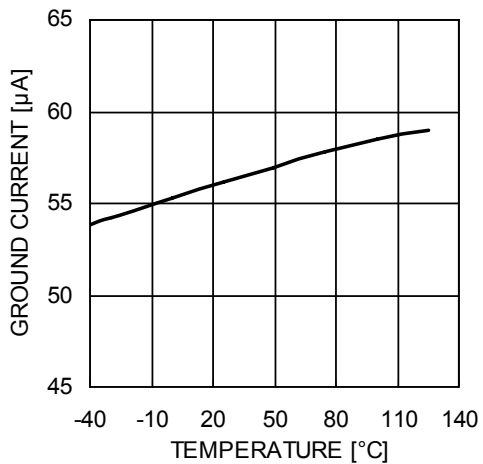
**Output Voltage vs. Temperature**



**Ground Current vs. Load Current**



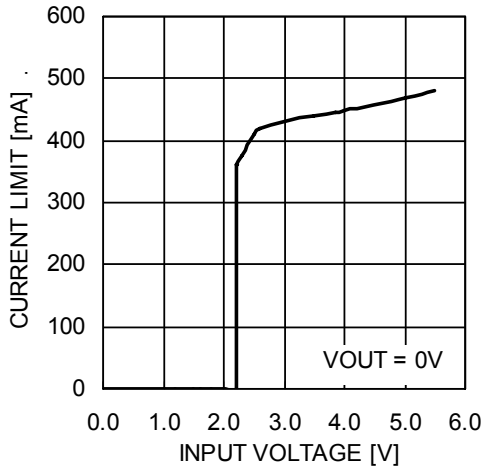
**Ground Current vs. Temperature**



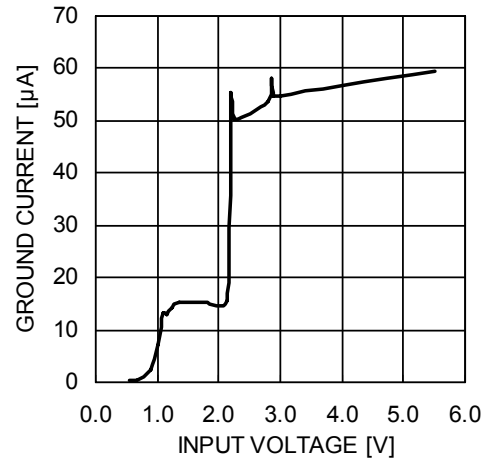
**TYPICAL CHARACTERISTICS** (shown for 2.85V output option)

$V_{IN} = 3.85V$ ,  $I_{OUT} = 100\mu A$ ,  $C_{IN} = C_{OUT} = 1\mu F$ ,  $C_{BYP} = 10nF$ ,  $T_A = 25^\circ C$  unless otherwise specified.

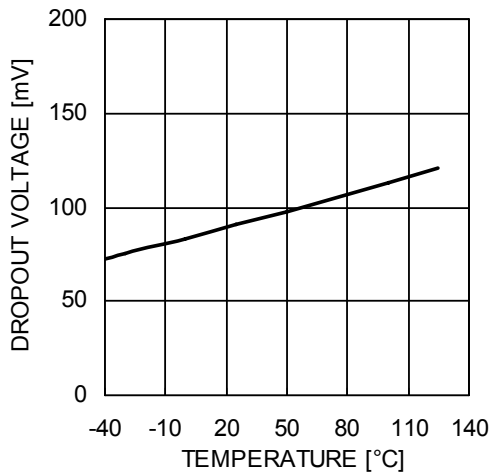
**Output Short-Circuit Current Limit**



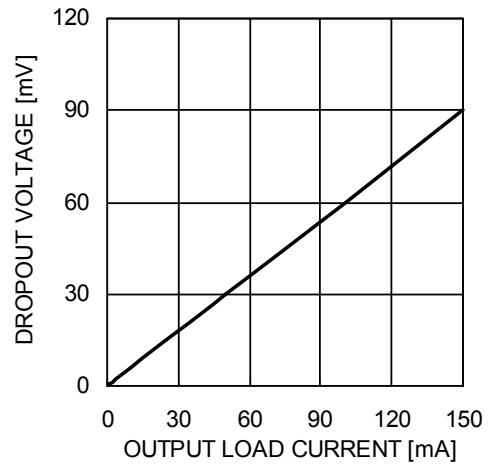
**Ground Current vs. Input Voltage**



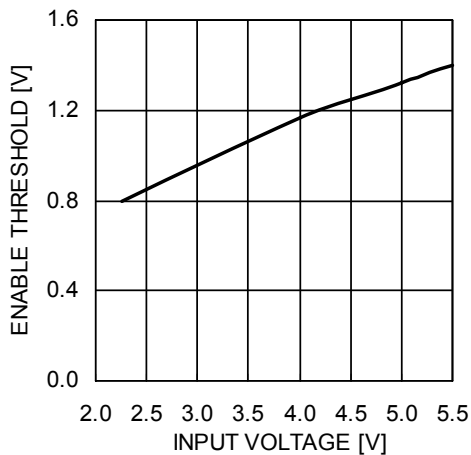
**Dropout vs. Temperature (150mA Load)**



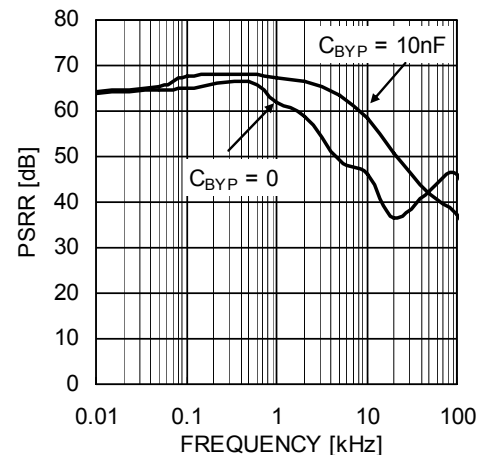
**Dropout vs. Load Current**



**Enable Threshold vs. Input Voltage**



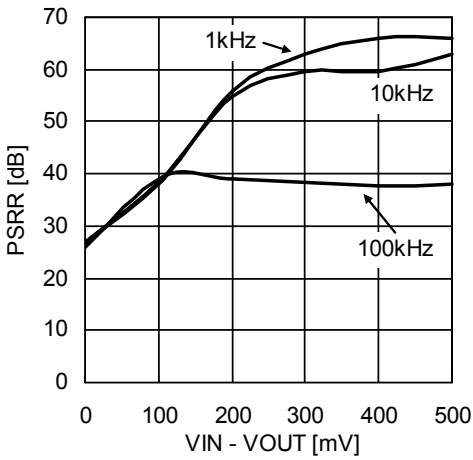
**PSRR vs. Frequency (10mA Load)**



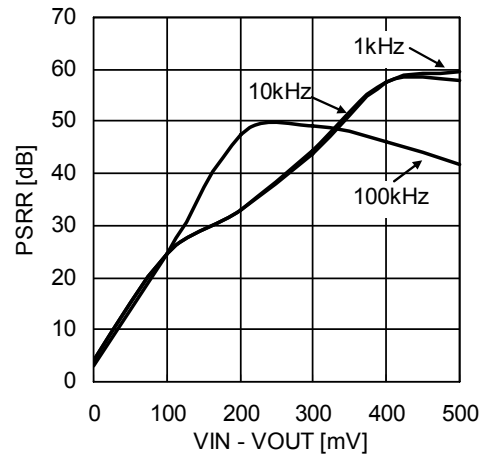
**TYPICAL CHARACTERISTICS** (shown for 2.85V output option)

$V_{IN} = 3.85V$ ,  $I_{OUT} = 100\mu A$ ,  $C_{IN} = C_{OUT} = 1\mu F$ ,  $C_{BYP} = 10nF$ ,  $T_A = 25^\circ C$  unless otherwise specified.

**PSRR (30mA Load)**



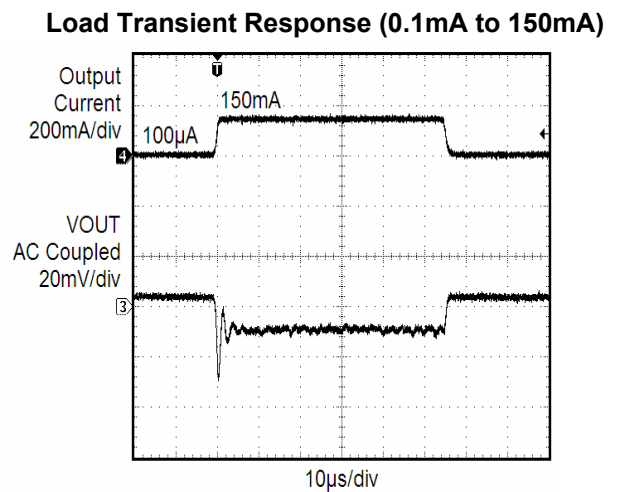
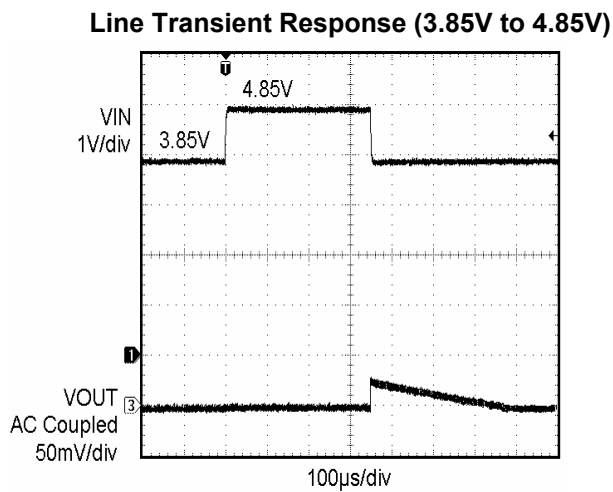
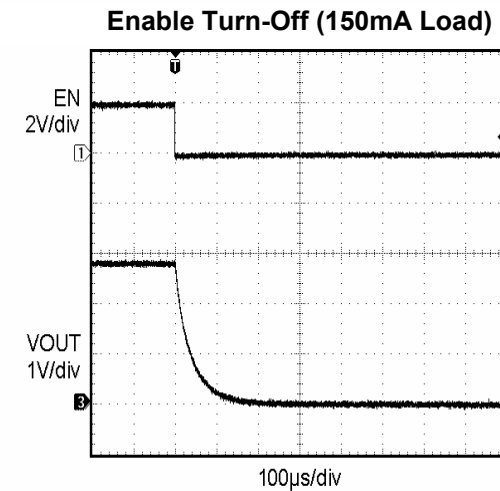
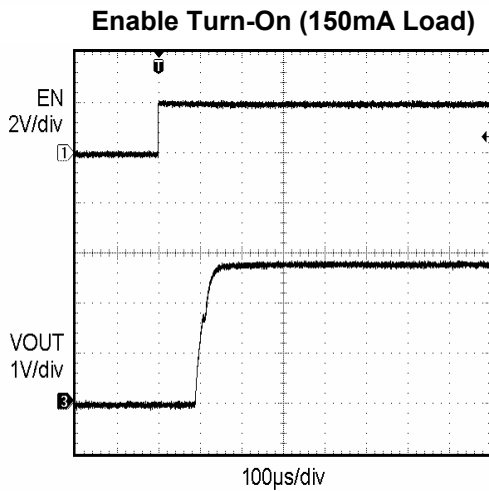
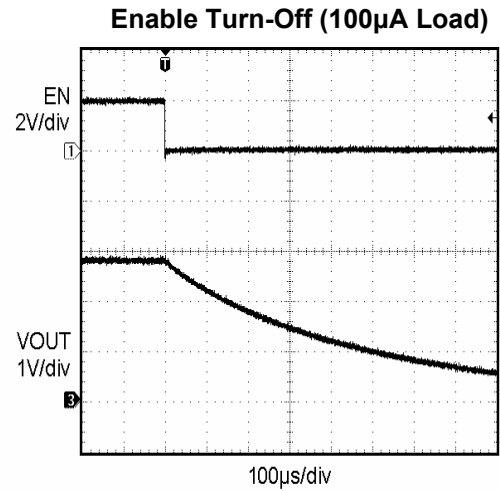
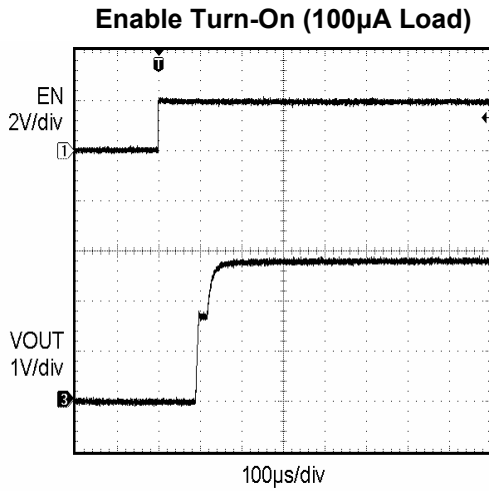
**PSRR (150mA Load)**



**TRANSIENT CHARACTERISTICS** (shown for 2.85V output option)

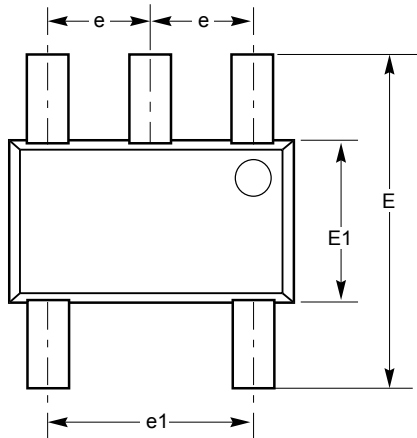
$V_{IN} = 3.85V$ ,  $I_{OUT} = 100\mu A$ ,  $C_{IN} = C_{OUT} = 1\mu F$ ,  $C_{BYP} = 10nF$ ,  $T_A = 25^\circ C$  unless otherwise specified.

**Note:** All transient characteristics are generated using the evaluation board CAT621XEVAL1.

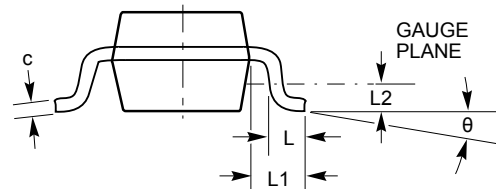
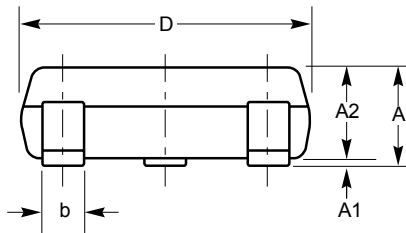


## PACKAGE OUTLINES

### 5-LEAD TSOT-23 <sup>(1)(2)</sup>



SYMBOL	MIN	NOM	MAX
A	—	—	1.00
A1	0.01	0.05	0.10
A2	0.80	0.87	0.90
b	0.30	—	0.45
c	0.12	0.15	0.20
D	2.90 BSC		
E	2.80 BSC		
E1	1.60 BSC		
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.40	0.50
L1	0.60 REF		
L2	0.25 BSC		
$\theta$	0°		8°



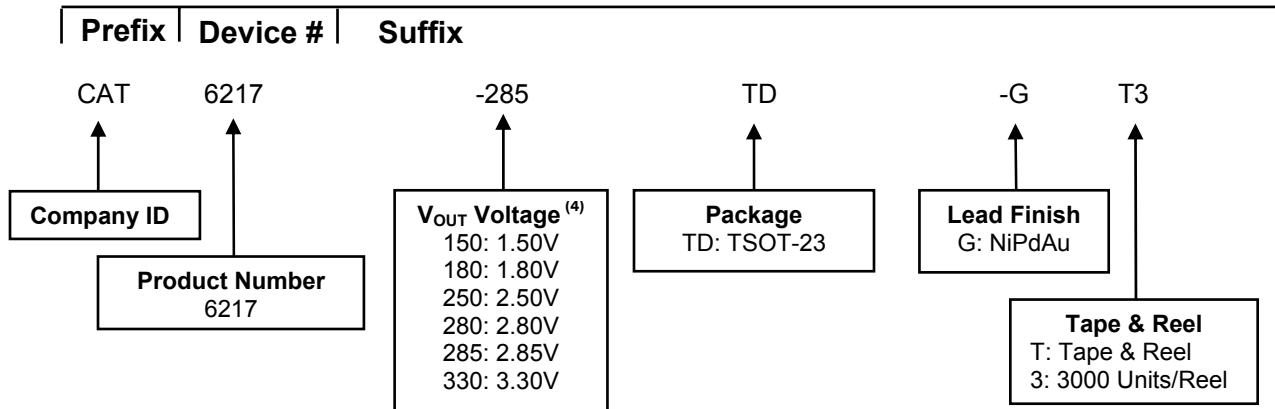
**2H**For current Tape and Reel information, download the PDF file from:

**Notes:**

- (1) All dimensions are in millimeters, angles in degrees.
- (2) Refer JEDEC MO-193.



**EXAMPLE OF ORDERING INFORMATION**



Ordering Number	V <sub>OUT</sub> Voltage	Package	Quantity per Reel
CAT6217-150TD-GT3	1.50V	TSOT-23	3000
CAT6217-180TD-GT3	1.80V	TSOT-23	3000
CAT6217-250TD-GT3	2.50V	TSOT-23	3000
CAT6217-280TD-GT3	2.80V	TSOT-23	3000
CAT6217-285TD-GT3	2.85V	TSOT-23	3000
CAT6217-330TD-GT3 <sup>(4)</sup>	3.30V	TSOT-23	3000

**Notes:**

- (1) All packages are RoHS-compliant (Lead-free, Halogen-free).
- (2) The standard finish is NiPdAu.
- (3) The device used in the above example is a CAT6217-285TD-GT3 (V<sub>OUT</sub> = 2.85V, in an TSOT-23 package, NiPdAu, Tape and Reel, 3000 units).
- (4) Standard voltages are 1.50V, 1.80V, 2.50V, 2.80V, and 2.85V. For other voltage options, please contact your nearest Catalyst Semiconductor Sales office.
- (5) Top marking for CAT6217 is RT.

## REVISION HISTORY

Date	Rev.	Reason
06/21/2007	A	Preliminary Revision

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